



# 6<sup>th</sup> International SemOI Conference and 1<sup>st</sup> Ukrainian-French Seminar “Semiconductor-On-Insulator materials, devices and circuits: physics, technology and diagnostics”

26-30 April 2010, Kyiv, Ukraine



## **FIRST ANNOUNCEMENT AND CALL FOR PAPERS**

### **Conference Objectives**

Goal of the Conference is to debate about the recent developments in nanometer down scaled Semiconductor-on-Insulator (SemOI) systems which are basis blocks for modern high-sensitive sensors in a wide range of applications such as telecommunications, radiation control, biomedical instrumentation, chemical analysis, etc. SemOI is foreseen as a key technology for the integration of high quality and resistant nanoscaled devices and integrated circuits which must operate in harsh environment. The goal of the Workshop will be realized by a program consisting of papers by **keynote speakers** who will provide reviews and by **speakers** who will present new research results.

### **The topics to be covered include the following:**

- Semiconductor-on-Insulator material technology
- Nanoscale CMOS devices and circuits
- New SemOI materials and devices on its basis
- SemOI sensors and new SemOI systems
- Diagnostic techniques for nanoscale SemOI materials and devices
- Technology and economics

### **Keynote speakers**

Prof. F.Balestra (IMEP-ENSERG, France); Prof. V.P.Bondarenko (BSUIR, Belarus); Prof. C.Colinge (California State University, USA); Prof. J.P.Colinge (Tyndall NI, Ireland); Prof. D.Flandre (UCL, Belgium); Prof. G.Gamble (Queen's Univ., Belfast, UK); Prof. F.Gamiz (Granada University, Spain); Prof. G.Ghibaudo (IMEP-LAHC, France); Prof. U.Goesele (MPI für Mikrostrukturphysik, Germany); Prof. S.Hall (University of Liverpool, UK); Prof. S.Ingebrandt (Univ. Appl. Sci. Kaiserslautern, Germany); Dr. M.Lemme (Harvard Univ., USA); Dr. C.Mazure (SOITEC, France); Prof. Martino (Univ. of Sao Paulo, Brazil); Prof. A.A.Orlikovsky (IPT RAS, Russia); Prof. J.P.Raskin (UCL, LLN, Belgium); Prof. F.F. Sizov (ISP, Ukraine); Prof. S.Roy (Univ. of Glasgow, UK)

### **Workshop key dates**

Deadline for Abstracts  
Notification to Authors  
Issue Preliminary Programme  
Deadline hotel reservations  
Workshop opens

**15 January 2010**  
**1 February 2010**  
**1 February 2010**  
**15 March 2010**  
**26 April 2010**

### **Paper submission**

Prospective authors should prepare 2-page summary of their work, including illustrations, suitable for reproduction in the Workshop Proceedings and submit 2 copies for review to organizers by **January 15, 2010**. Proceedings (consisting of a copy of all abstracts) will be handed out to all attendees at the Workshop.

Comprehensive instruction for abstract preparation see on the next page.

If you are planning to attend the workshop or present a paper, please send your name and contact details to the organizers. Conference registration and hotel information will only be sent to those who respond.

### **Organized by**

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### **International Organizing Committee**

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**S. Hall** (Univ. Liverpool, UK)

**V.S. Lysenko** (ISP, Ukraine)

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## Preparation of Abstract

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This set of instructions is given in the style and format to be used by authors in preparing “camera-ready” abstracts. Please follow the instructions listed below. Abstract must be prepared in English.

### Total length of Abstract

The total length of the abstract, including all text, graphs, tables, charts, drawing and pictures, is *two pages*.

### Printout

The most suitable printer is laser/jet. The printout submitted should be an original; a photocopy is not acceptable. Please make use of good quality plain white A4 paper size.

### Size

The abstract must be typed within the frame shown (16 x 25 cm<sup>2</sup>); the frame must not appear on the summary. Margins on the top, bottom, left and right are thus 2cm, 2cm, 3cm and 2cm, respectively, as shown on this template. The title shall be bold, centered at the top of the page and followed by the name(s) of the author(s) and their affiliation. We recommend the use of 1.0 (single) line spacing. In these instructions we use the Times New Roman font. If you cannot produce an output in Times New Roman, choose a font on your system that is similar. The font size used in the abstract should be no smaller than 10 point. Tables, graphs and figures may be smaller if legible. References should be collected at the end of your paper.

### Pictures

Half-tone copies of black and white photographs are preferable for reproduction; however, if this is not possible, please understand that the quality may be degraded.

### Cover letter

Please submit 2 copies of your abstracts with a cover letter identifying the contact author, mailing address, telephone number, FAX number, and e-mail address (if available).

### Notification

You will be notified by **5 February 2010** whether your paper is accepted for the Workshop. If your paper is accepted you will receive instructions for preparing camera-ready manuscripts.